

# Silicon Carbide MOSFET

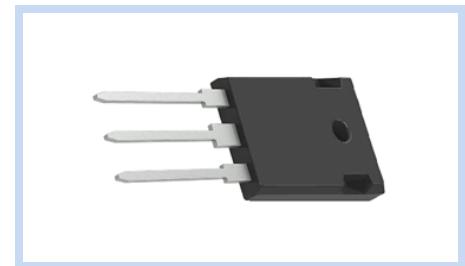
## N-Channel 1700V 72A TO-247

MFTC170N72T247

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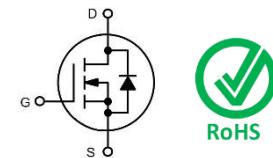
### FEATURE

- $R_{DS(ON)} < 70\text{m}\Omega$  at  $V_{GS}=20\text{V}$ ,  $I_D=50\text{A}$
- Low On-Resistance with High Blocking Voltage
- Low Capacitances with High-Speed Switching
- Easy to Parallel and Simple to Drive
- Applications: High Voltage DC/DC Converters, Switching Mode Power Supplier, Solar Inverters, Motor Drivers



### MECHANICAL DATA

- Case: TO-247 Package
- Terminals: Solderable per MIL-STD-750, Method 2026



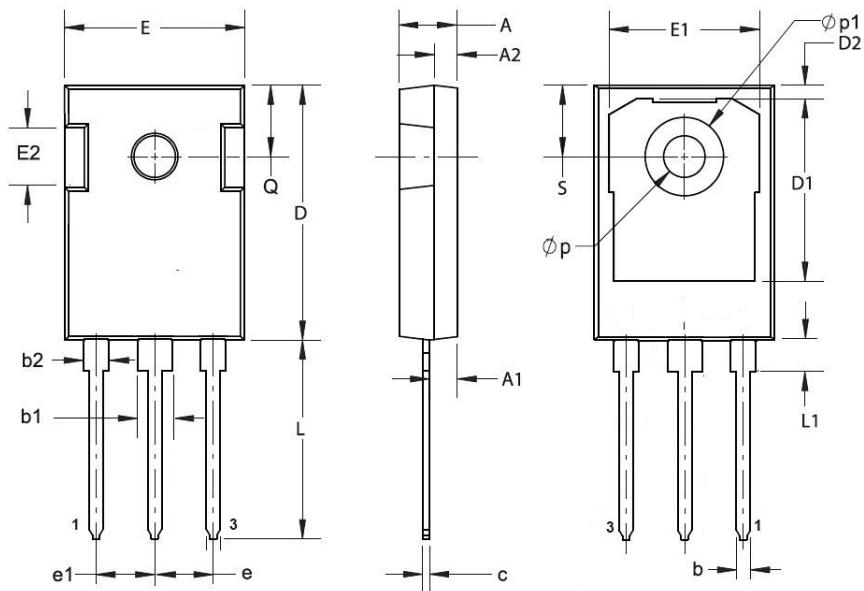
### MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	1700	V
Gate-Source Voltage	$V_{GS}$	-10/+25	V
		-5/+20	
Drain Current – Continuous	$I_D$	72	A
		48	
Drain Current – Pulse with $t_p$ Limited by $T_{jmax}$	$I_{DM}$	160	A
Power Dissipation	$P_D$	520	W
Thermal Resistance, Junction to Case	$R_{eJC}$	0.24	$^{\circ}\text{C} / \text{W}$
Thermal Resistance, Junction to Ambient	$R_{eJA}$	40	$^{\circ}\text{C} / \text{W}$
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^{\circ}\text{C}$

### DIMENSIONS

DIMENSION	Min	Max
A	4.80	5.20
A1	2.25	2.55
A2	0.55	0.70
b	1.05	1.35
b1	2.85	3.40
b2	1.91	2.21
c	0.55	0.70
D	20.8	21.2
D1	16.25	17.65
e	5.44 BSC	
e1	5.44 BSC	
E	15.70	16.20
L	19.80	20.35
L1	4.00	4.50
p	3.40	3.80
p1	7.180 BSC	
Q	6.15 BSC	

Note: Pin Layout: 1:Gate(G), 2:Drain(D), 3:Source(S)



## ELECTRICAL CHARACTERISTICS

Off Characteristics	Conditions	Symbol	Min	Typ.	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=100\mu A$	$BV_{DSS}$	1700	--	--	V
Zero Gate Voltage Drain Current	$V_{DS}=1700V, V_{GS}=0V$	$I_{DSS}$	--		100	$\mu A$
Gate-Body Leakage Current, Forward	$V_{GS}=25V, V_{DS}=0V$	$I_{GSSF}$	--		250	nA
Gate-Body Leakage Current, Reverse	$V_{GS}=-10V, V_{DS}=0V$	$I_{GSSR}$	--		250	nA
On Characteristics	Conditions	Symbol	Min	Typ.	Max	Unit
Static Drain-Source On-Resistance	$V_{GS}=20V, I_D=50A$	$R_{DS(ON)}$	--	45	70	$m\Omega$
	$V_{GS}=20V, I_D=50A, T_J=150^\circ C$		--	90	--	
Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=18mA$	$V_{GS(th)}$	2.0	--	4.0	V
	$V_{GS}=V_{DS}, I_D=18mA, T_J=150^\circ C$		--	1.8	--	
Transconductance	$V_{GS}=20V, I_D=50A$	$g_{FS}$	--	25.8	--	S
	$V_{GS}=20V, I_D=50A, T_J=150^\circ C$		--	27	--	
Dynamic Characteristics	Conditions	Symbol	Min	Typ.	Max	Unit
Total Gate Charge		$Q_g$	--	193	--	nC
Gate-Source Charge	$V_{DS}=1200V, I_D=50A, V_{GS} = -5/+20V$	$Q_{gs}$	--	54	--	
Gate-Drain Charge		$Q_{gd}$	--	25	--	
Turn-On Delay Time		$T_{d(on)}$	--	27	--	nS
Rise Time	$V_{DS}=1200V, I_D=30A, R_L=20\Omega$ $V_{GS} = -5/+20V, R_{GEN}=2.5\Omega,$	$T_r$	--	32	--	
Turn-Off Delay Time		$T_{d(off)}$	--	36	--	
Fall Time		$T_f$	--	10	--	
Turn-On Switching Loss	$V_{DS}=1200V, I_D=30A, L=100\mu H$ $V_{GS} = -5/+20V, R_{GEN}=2.5\Omega,$	$E_{ON}$	--	3.1	--	mJ
Turn-Off Switching Loss		$E_{OFF}$	--	1.1	--	
$C_{oss}$ Stored Loss		$E_{oss}$	--	101	--	$\mu J$
Input Capacitance	$V_{DS}=1000V, V_{GS}=0V, V_{AC}=25mV$ $f=1MHz$	$C_{iss}$	--	3550	--	pF
Output Capacitance		$C_{oss}$	--	165	--	
Reverse Transfer Capacitance		$C_{rss}$	--	6.1	--	
Internal Gate Resistance	$V_{AC}=25mV, f=1MHz$	$R_{G(int)}$	--	2.6	--	$\Omega$
Drain-Source Body Diode	Conditions	Symbol	Min	Typ.	Max	Unit
Diode Forward Current	$T_C=25^\circ C$	$I_s$	--	--	72	A
Drain-Source Diode Forward Voltage	$V_{GS} = -5V, I_{SD}=25A$	$V_{SD}$	--	4.5	--	V
	$V_{GS} = -5V, I_{SD}=25A, T_J=150^\circ C$		--	4.2	--	
Peak Reverse Recovery Current		$I_{rm}$	--	6.7	--	A
Reverse Recovery Time	$V_R=1200V, I_{SD}=50A$	$T_{rr}$	--	55	--	nS
Reverse Recovery Charge		$Q_{rr}$	--	220	--	nC

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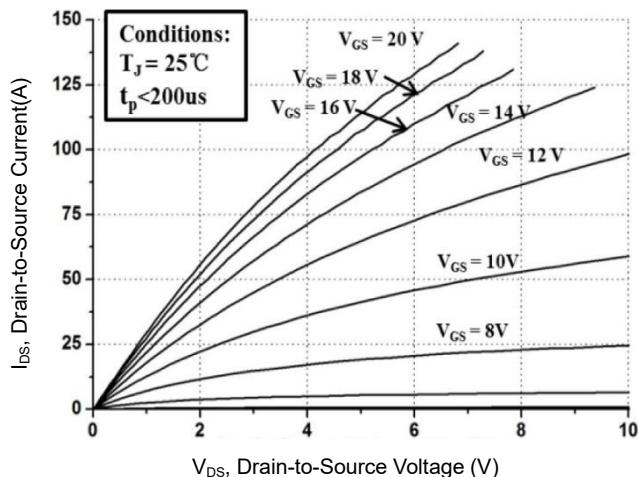
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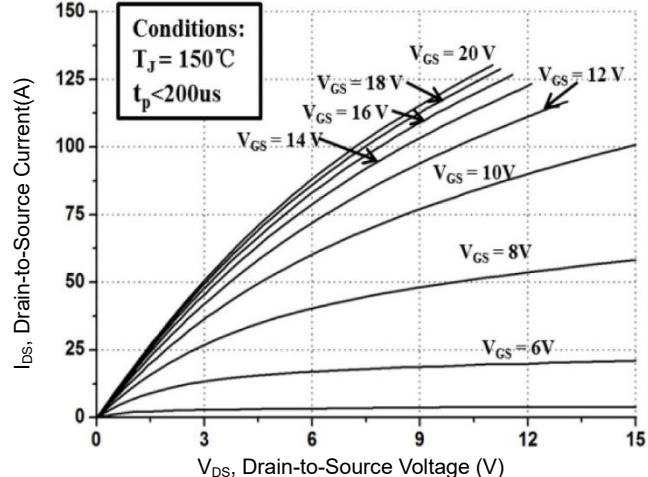
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### CHARACTERISTIC CURVES

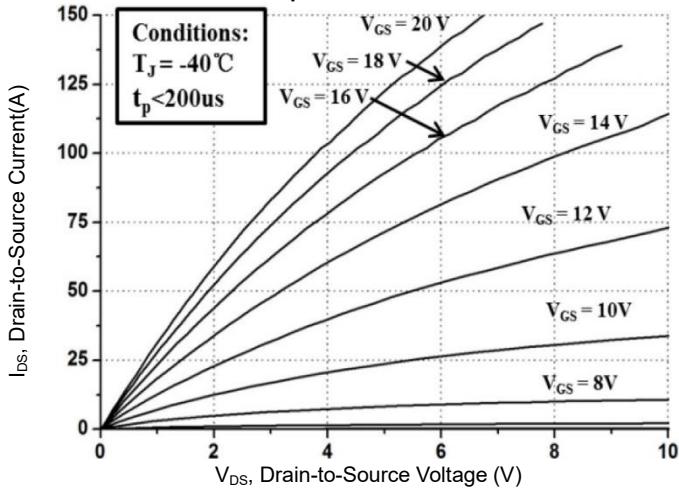
Output Characteristics



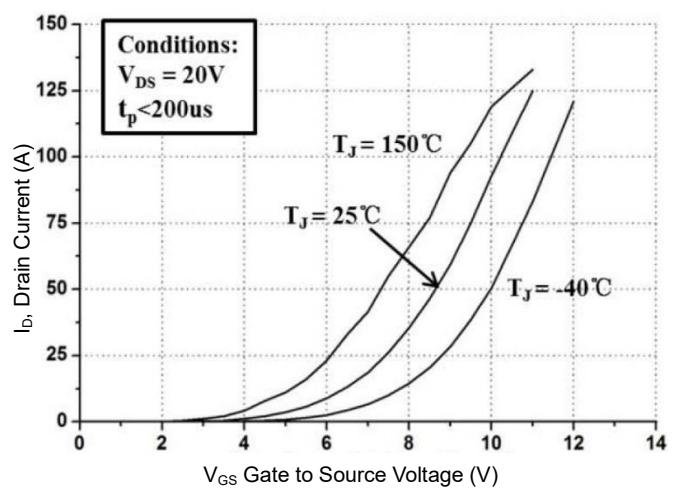
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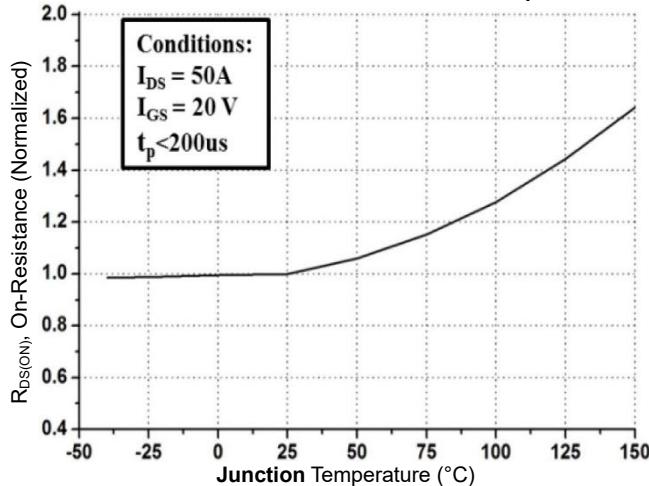
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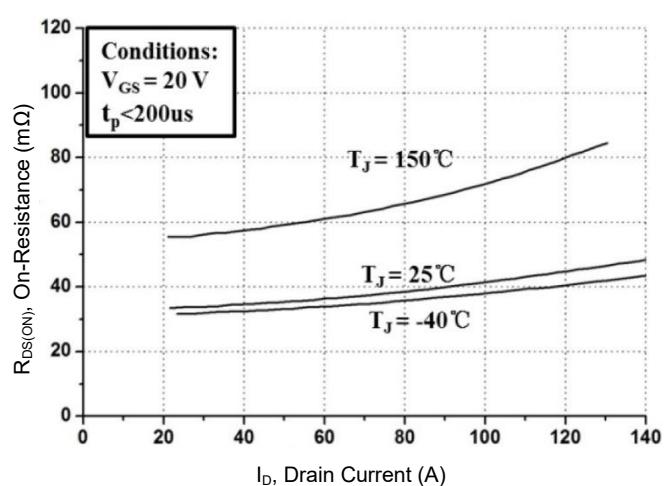
Transfer Characteristic



Normalized On-Resistance vs. Junction temperature



On-Resistance vs. Drain Current



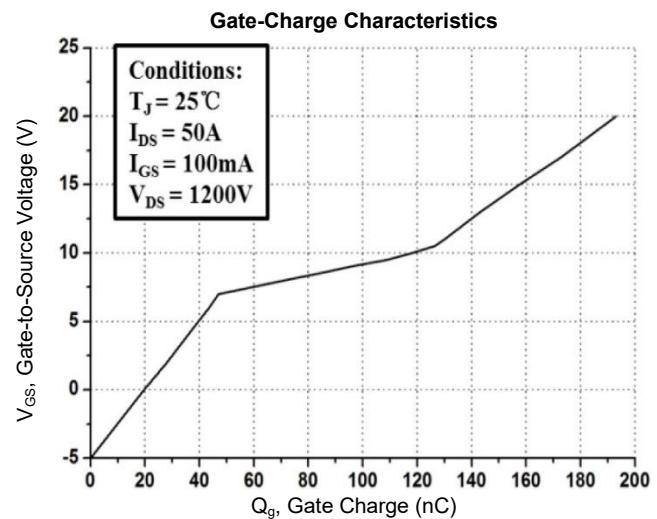
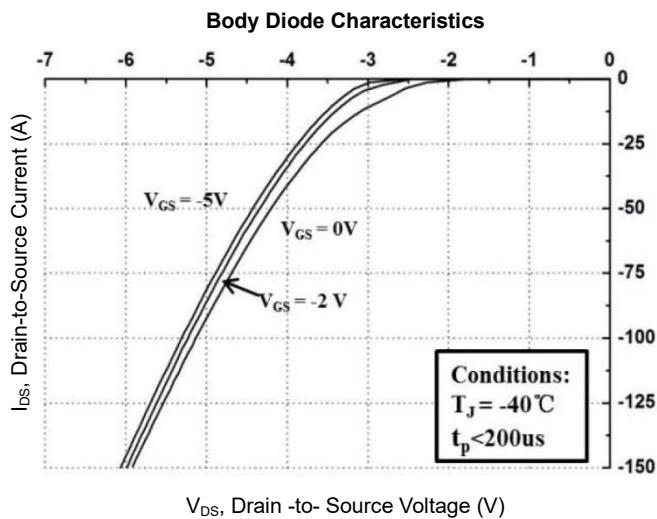
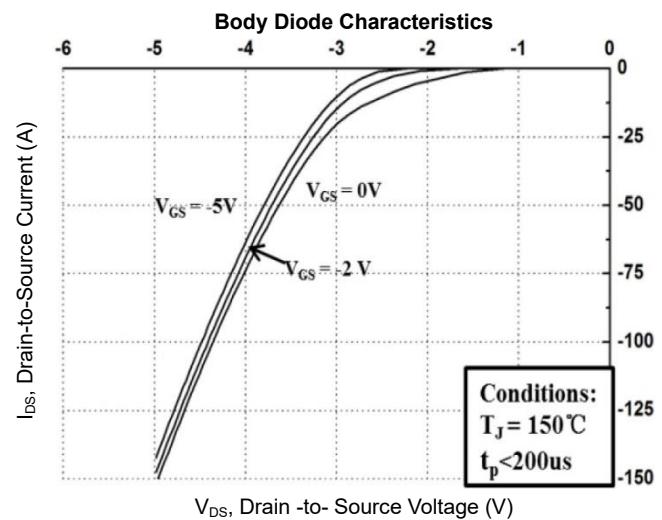
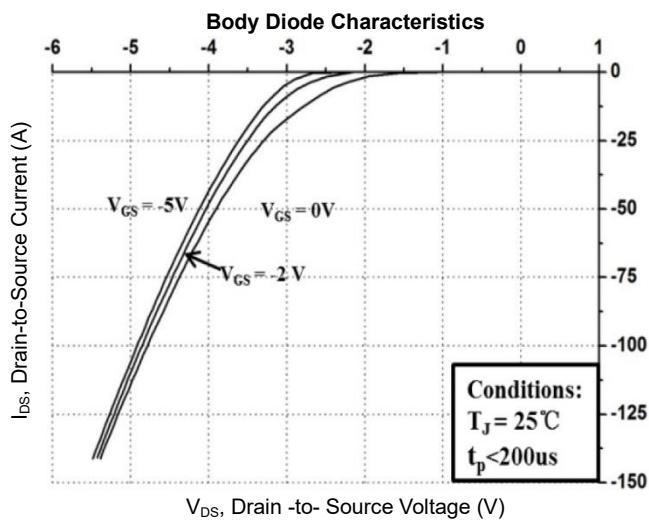
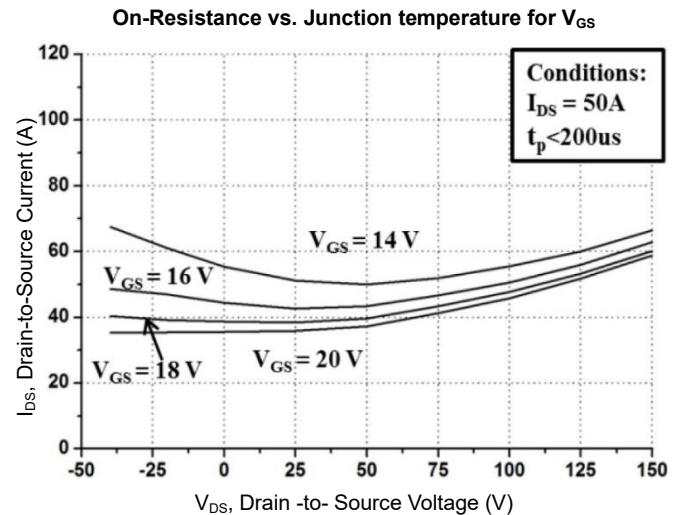
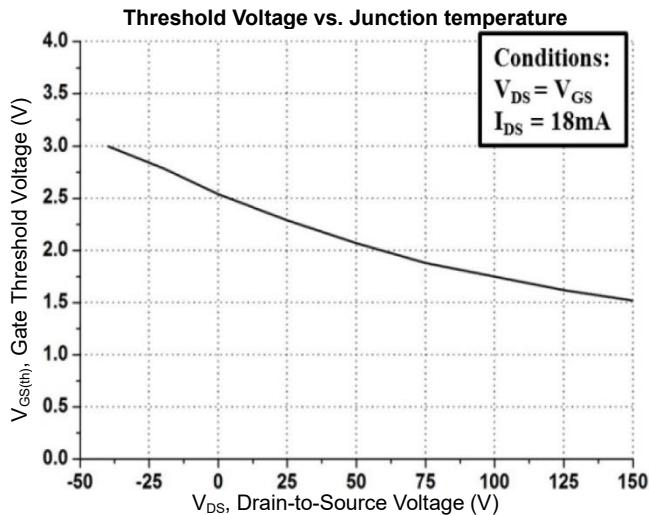
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